

PSMNR90-80ASE

N-channel, 80 V, 0.9 mOhm, MOSFET with enhanced SOA in CCPAK1212 package

3 May 2024

Objective data sheet

1. General description

N-channel enhancement mode MOSFET in a CCPAK1212 package qualified to 175 °C. Part of Nexperia's Application Specific MOSFETs (ASFETs) for Hotswap and Soft Start. The PSMNR90-80ASE delivers very low R_{DSon} and enhanced safe operating area performance in a high-reliability copper-clip package (CCPAK1212).

PSMNR90-80ASE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn-on, low R_{DSon} to minimize I²R losses and deliver optimum efficiency when turned fully ON.

2. Features and benefits

- Fully optimized Safe Opertating Area (SOA) for superior linear mode operation
- Low R_{DSon} for low I²R conduction losses
- CCPAK1212 package for applications that demand the highest performance and reliability

3. Applications

- Hot swap
 - Load switch
- Soft start
- E-fuse
- Telecommunication systems based on a 48 V backplane/supply rail

4. Quick reference data

Parameter	Conditions		Min	Тур	Max	Unit
Irain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	80	V
frain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	-	400	А
otal power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	1.071	kW
unction temperature			-55	-	175	°C
stics			!	_		
drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	0.71	0.9	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C		-	[tbd]	[tbd]	mΩ
teristics		_			-	_
ate-drain charge	I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V;		-	46	-	nC
otal gate charge	T _j = 25 °C; <u>Fig. 2</u>		[tbd]	286	[tbd]	nC
edness			i			-
non-repetitive drain- source avalanche energy	I_D = 129 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[2]	-	-	1781	mJ
	Irain current otal power dissipation unction temperature stics Irain-source on-state esistance teristics pate-drain charge otal gate charge edness ion-repetitive drain- ource avalanche	Irain current $V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}$ otal power dissipation $T_{mb} = 25 \text{ °C}; \text{ Fig. 1}$ unction temperature $T_{mb} = 25 \text{ °C}; \text{ Fig. 1}$ sticsIrain-source on-state esistance $V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 25 \text{ °C}$ $V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 175 \text{ °C}$ $V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 175 \text{ °C}$ teristicsID = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};pate-drain chargeID = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};otal gate chargeTj = 25 °C; Fig. 2ednessID = 129 \text{ A}; V_{sup} \leq 80 \text{ V}; \text{ R}_{GS} = 50 \Omega;ource avalancheID = 129 \text{ A}; V_{sup} \leq 80 \text{ V}; \text{ R}_{GS} = 50 \Omega;	Irain current $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}$ [1]otal power dissipation $T_{mb} = 25 \text{ °C}; Fig. 1$ Image: constant of the second	$\begin{array}{c c c c c c } \mbox{Irain current} & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^{\circ}C & [1] & - \\ \mbox{otal power dissipation} & T_{mb} = 25 \ ^{\circ}C; \ \underline{Fig. 1} & - \\ \mbox{unction temperature} & -55 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Irain current $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}$ [1]otal power dissipation $T_{mb} = 25 \text{ °C}; Fig. 1$ unction temperature-55-sticsIrain-source on-state esistance $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$ -0.71 $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C}$ -0.71teristicspate-drain charge $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ -46teristicspate-drain charge $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ -46obal gate charge $T_j = 25 \text{ °C}; Fig. 2$ [Ibd]286ednessnon-repetitive drain- ource avalanche $I_D = 129 \text{ A}; V_{sup} \le 80 \text{ V}; R_{GS} = 50 \Omega;$ $V_{GS} = 10 \text{ V}; T_j(init) = 25 \text{ °C}; unclamped$	Irain current $V_{GS} = 10 \text{ V}; T_{mb} = 25 ^{\circ}\text{C}$ [1] - - 400 otal power dissipation $T_{mb} = 25 ^{\circ}\text{C}; Fig. 1$ - - 1.071 unction temperature -55 - 175 stics Irain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}$ - 0.71 0.9 vGs = 10 V; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C} - [Ibd] [Ibd] [Ibd] teristics Interistics Interistics - - 46 - pate-drain charge Interistics Interistics - 46 - pate-drain charge Interistics - 46 - pate-drain charge Interistics - - 46 - pate-drain charge Interistics - - 46 - potal gate charge Interistics - - 46 - potal gate charge Interistics - - 1781 - potal gate charge Interistics - - 1781 -

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PSMNR90-80ASE

N-channel, 80 V, 0.9 mOhm, MOSFET with enhanced SOA in CCPAK1212 package

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Source-drain d	iode						
Qr		$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 40 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 3}$	[3]	-	108	-	nC

[1] Max current will be demonstrated through application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test

[3] includes capacitive recovery

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	S	source		
4	S	source	12 11 10 9 8 7	
5	S	source		
6	S	source		D
7	D	drain		
8	D	drain		G
9	D	drain	<u>beeee</u>	mbb076 S
10	D	drain	1 2 3 4 5 6 CCPAK1212 (SOT8000A)	
11	D	drain	CCPAR 1212 (SU10000A)	
12	D	drain		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMNR90-80ASE		Plastic, surface mounted copper clip package (CCPAK1212); 13 terminals; 2.0 mm pitch, 12 mm x 12 mm x 2.5 mm body	SOT8000A		

7. Limiting values

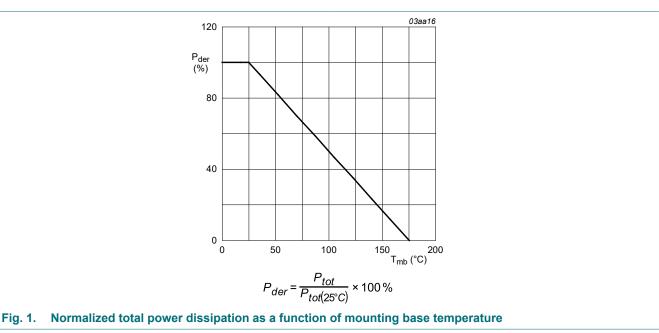
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). T_i = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	80	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	1.071	kW
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	400	А
		V _{GS} = 10 V; T _{mb} = 100 °C		-	282	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1600	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode		·			
I _S	source current	T _{mb} = 25 °C		-	400	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1600	А
Avalanche r	uggedness				·	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 129 A; $V_{sup} \le 80$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[2]	-	1781	mJ

 Max current will be demonstrated through application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	[tbd]	0.14	K/W

PSMNR90-80ASE

9. Characteristics

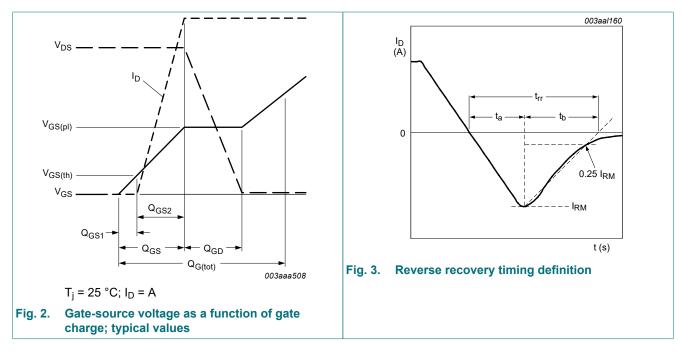
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static charac	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _i = -55 °C	72	-	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	2	2.6	3.6	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C	-	1.6	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C	-	3	-	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	[tbd]	-	mV/k
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	[tbd]	5	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	[tbd]	[tbd]	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
			-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	0.71	0.9	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C	-	[tbd]	[tbd]	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C	-	[tbd]	[tbd]	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	[tbd]	2.7	[tbd]	Ω
Dynamic cha	aracteristics		I			
Q _{G(tot)} total gate charge	total gate charge	$\label{eq:ID} \begin{array}{ c c c c c c c c c c c c c c c c c c c$	[tbd]	286	[tbd]	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	148	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 2}}{2}$	[tbd]	115	[tbd]	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	68	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	47	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 2}}{2}$	-	46	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 40 V; T _j = 25 °C	-	[tbd]	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 0.5 MHz;	[tbd]	24703	[tbd]	pF
C _{oss}	output capacitance	T _j = 25 °C	[tbd]	5434	[tbd]	pF
C _{rss}	reverse transfer capacitance	1	[tbd]	81	[tbd]	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R _L = 1.6 Ω; V _{GS} = 10 V;	-	90	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	75	-	ns
t _{d(off)}	turn-off delay time	1	-	169	-	ns
t _f	fall time	1	-	88	-	ns
Source-drain	n diode	, I	1			
		I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C				V

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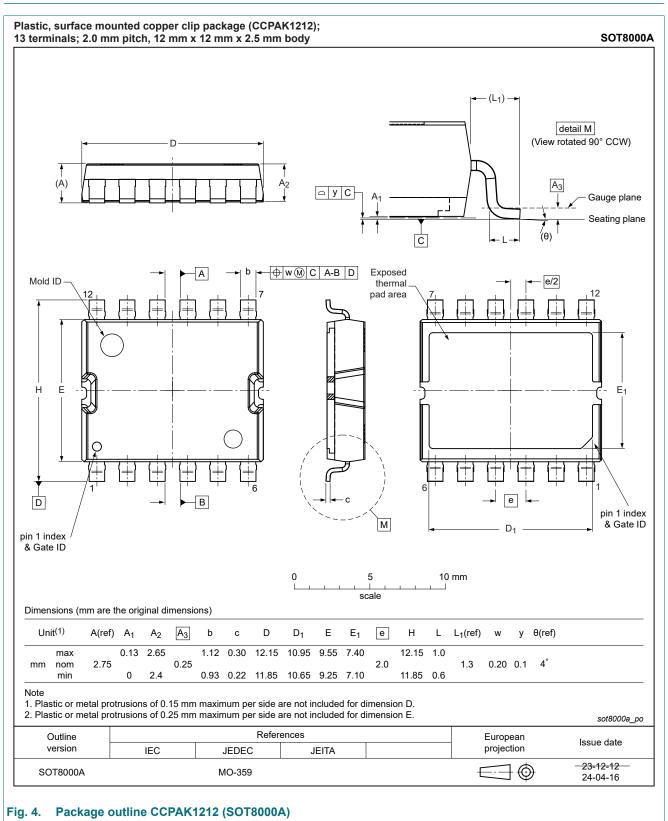
N-channel, 80 V, 0.9 mOhm, MOSFET with enhanced SOA in CCPAK1212 package

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
t _{rr}		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	85	-	ns
Q _r	recovered charge	V _{DS} = 40 V; T _j = 25 °C; <u>Fig. 3</u>	[1]	-	108	-	nC

[1] includes capacitive recovery



10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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